



CPH6339 — P-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- High-speed switching.
- 4V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-45	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		-3	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-12	A
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.6	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =-1mA, V _{GS} =0V	-45			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-45V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-1.5A	2.0	3.4		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-1.5A, V _{GS} =-10V		82	107	mΩ
	R _{DS(on)2}	I _D =-1A, V _{GS} =-4.5V		128	180	mΩ
	R _{DS(on)3}	I _D =-1A, V _{GS} =-4V		140	196	mΩ

Marking : YR

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CPH6339

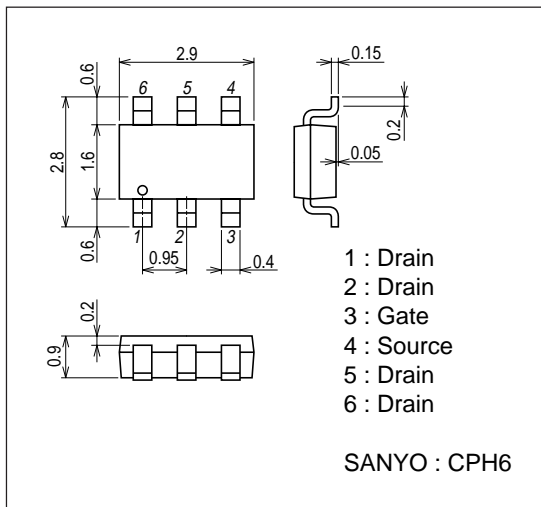
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V _{DS} =-20V, f=1MHz		680		pF
Output Capacitance	Coss	V _{DS} =-20V, f=1MHz		75		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-20V, f=1MHz		50		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		10		ns
Rise Time	t _r	See specified Test Circuit.		12		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		54		ns
Fall Time	t _f	See specified Test Circuit.		27		ns
Total Gate Charge	Qg	V _{DS} =-24V, V _{GS} =-10V, I _D =-3A		14		nC
Gate-to-Source Charge	Qgs	V _{DS} =-24V, V _{GS} =-10V, I _D =-3A		2.2		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =-24V, V _{GS} =-10V, I _D =-3A		2.9		nC
Diode Forward Voltage	V _{SD}	I _S =-3A, V _{GS} =0V	-0.85		-1.2	V

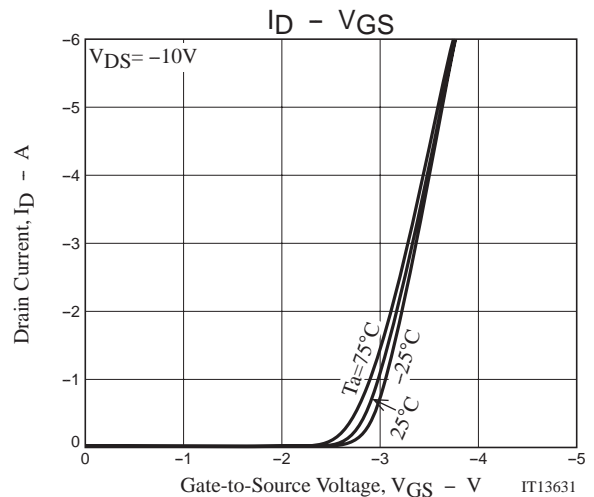
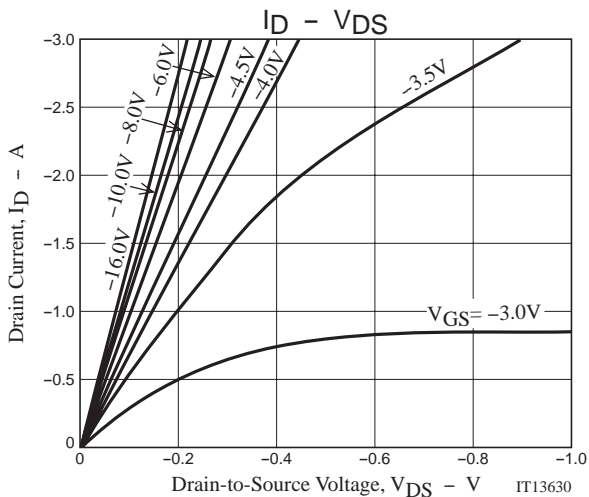
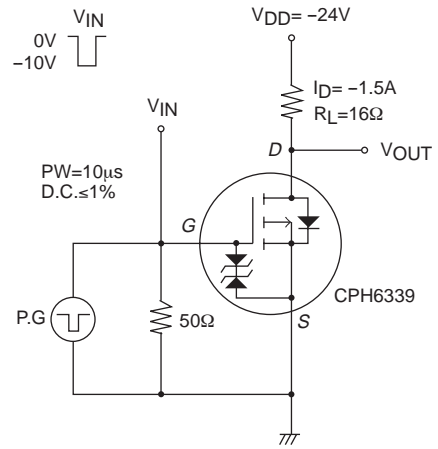
Package Dimensions

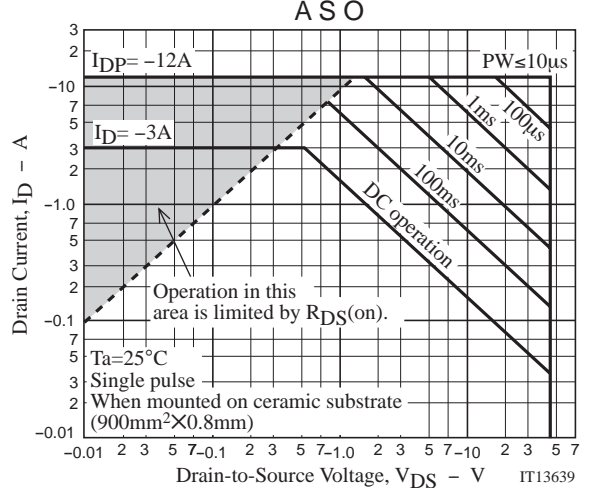
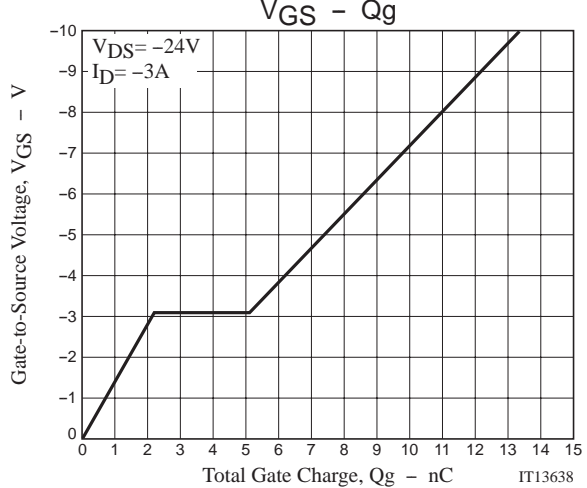
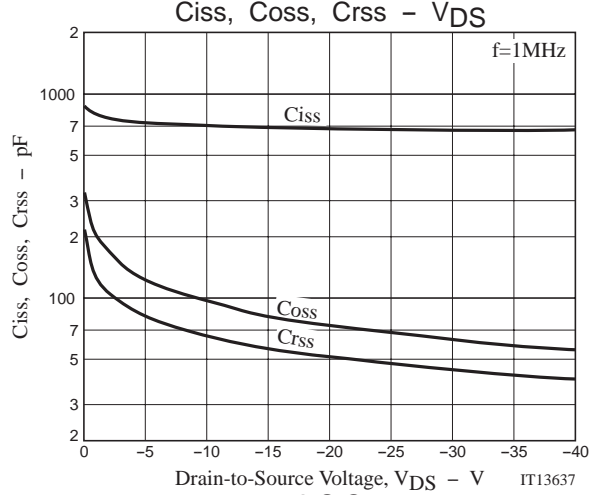
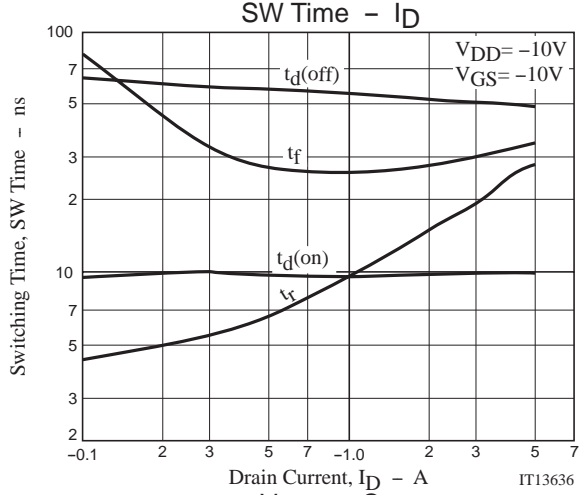
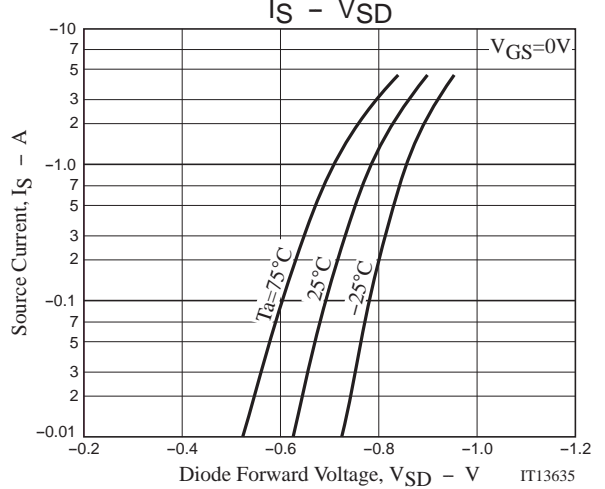
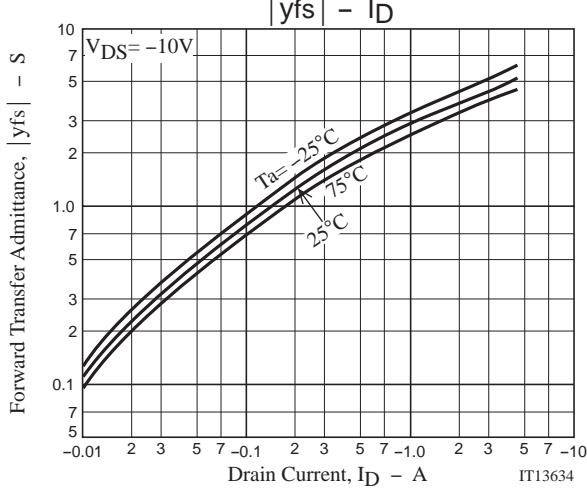
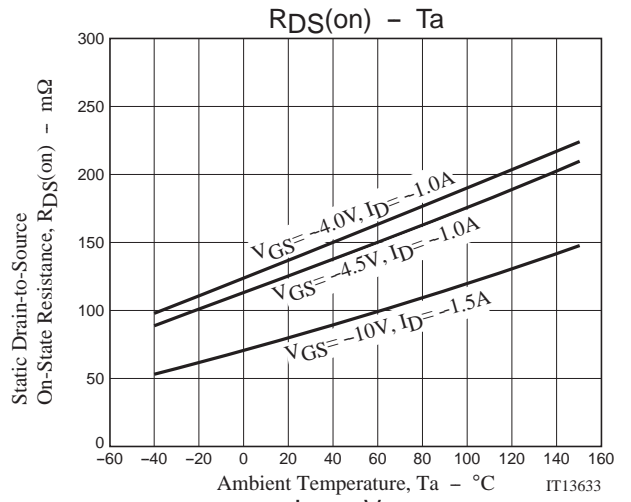
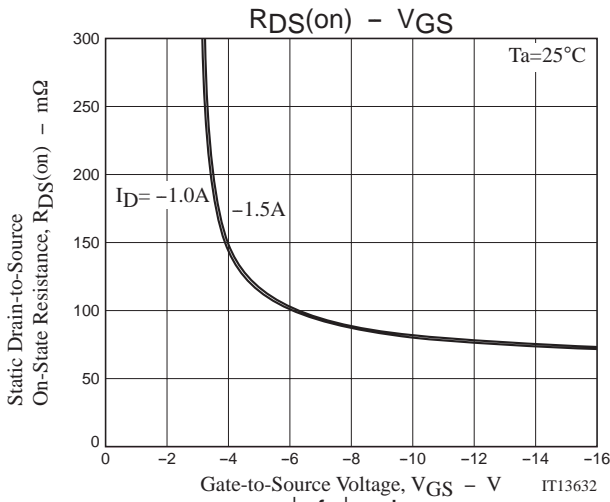
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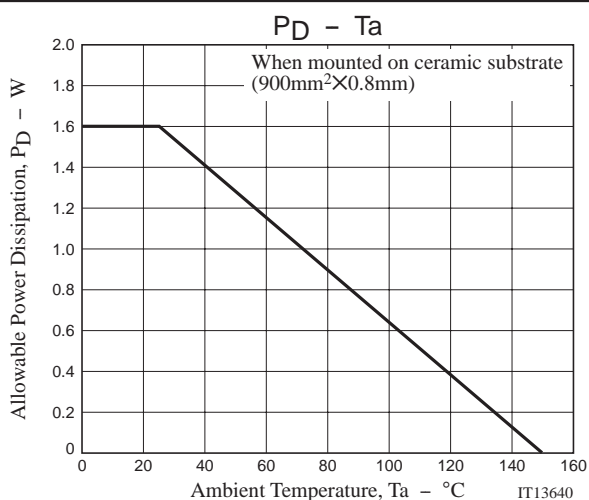
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Switching Time Test Circuit







Note on usage : Since the CPH6339 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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